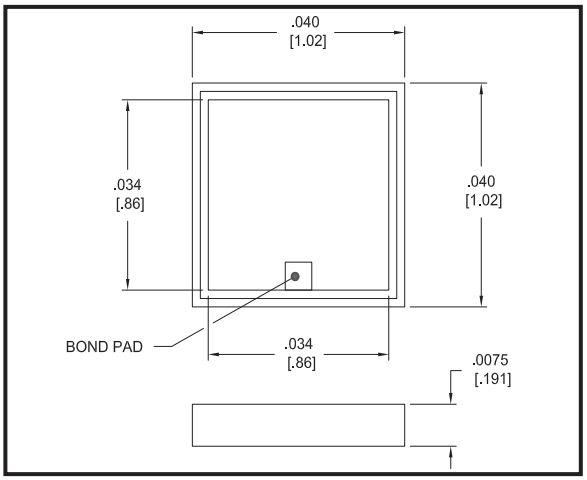


FEATURES

- Near Infrared Reduced Footprint Photodiode
- Photosensitive active area: 0.86mm x 0.86mm
- High Sensitivity: 0.65 A/W (ʎ=850nm)
- Wide Operating Temperature: -55°C TO 100°C
- Ideal for High Volume Laser Monitoring Applications
- RoHS and REACH Compliant

Dimensions are in inch [metric] units.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

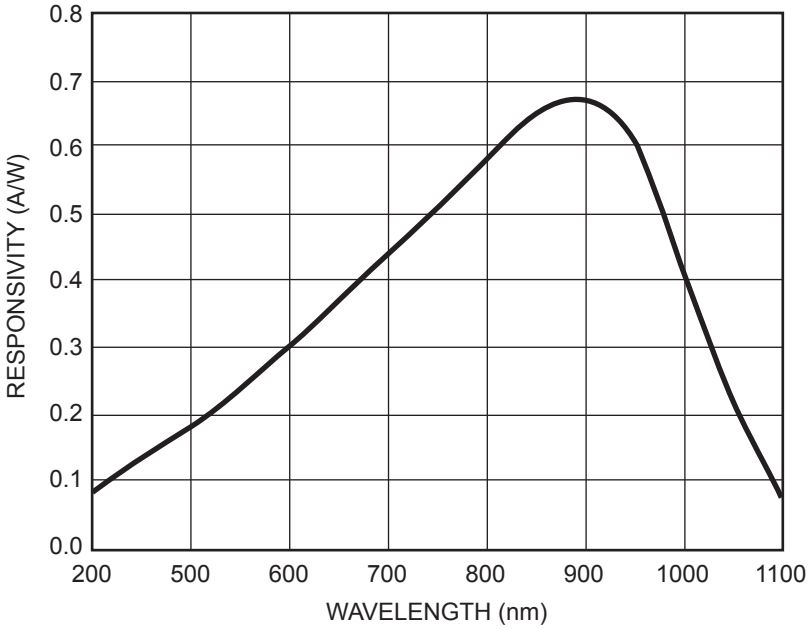
PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area			0.74		mm^2
Responsivity, $\mathcal{R}$	@ 850nm		0.65		A/W
Shunt Resistance	V_R = 10mV	200			MΩ
Reverse Breakdown Voltage, V_R	I_R = 10μA	25			Volts
Capacitance, C	V_R = 0V			8	pF
Rise Time	V_R = 10V			15	nsec

THERMAL PARAMETERS

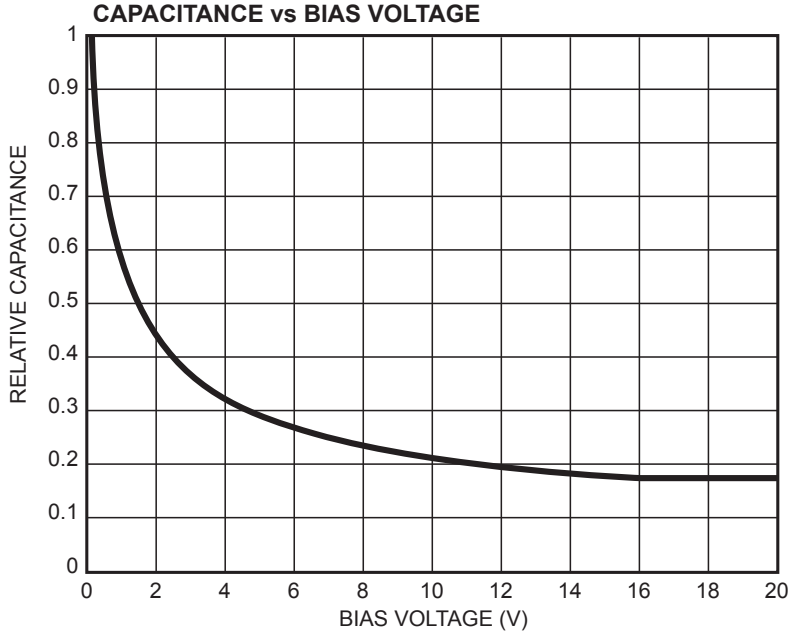
Storage and Operating Range	–55°C TO 100°C
Maximum Junction Temperature	100°C

OPTO DIODE
1260 Calle Suerte, Camarillo, California 93012
Phone: (805) 499-0335, Fax: (805) 499-8108
Email: sales@optodiode.com, Website: www.optodiode.com

TYPICAL SPECTRAL RESPONSE



CAPACITANCE vs BIAS VOLTAGE



ORDERING INFORMATION

ODD-850-005-1 Waffle Pack
ODD-850-005-2 Grip Ring

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